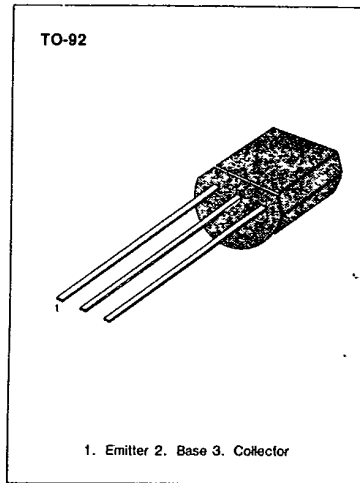


KSC839**NPN EPITAXIAL SILICON TRANSISTOR**

T-31-17

FM/AM RADIO RF AMP, CONV, OSC, IF AMP• Current-Gain-Bandwidth Product $f_T = 200\text{MHz}$ **ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	35	V
Collector-Emitter Voltage	V_{CE0}	30	V
Emitter-Base Voltage	V_{EB0}	4	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	250	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 - 150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)**

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = 100\mu\text{A}, I_E = 0$	35			V
Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C = 5\text{mA}, I_B = 0$	30			V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = 10\mu\text{A}, I_C = 0$	4			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 30\text{V}, I_E = 0$			0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 12\text{V}, I_C = 2\text{mA}$	40		400	
Base-Emitter On Voltage	$V_{BE}(on)$	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	0.65	0.70	0.75	V
Collector-Emitter Saturation Voltage	$V_{CE}(sat)$	$I_C = 10\text{mA}, I_B = 1\text{mA}$		0.1	0.4	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	80	200		MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0$ $f = 1\text{MHz}$		2.0	3.5	pF

 h_{FE} CLASSIFICATION

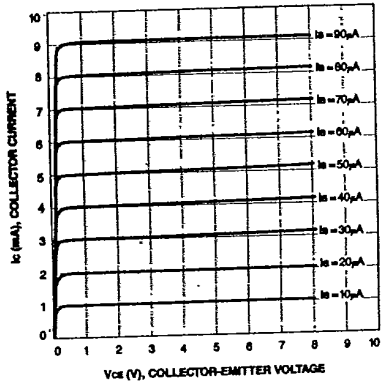
Classification	R	O	Y	G
h_{FE}	40-80	70-140	120-240	200-400

KSC839

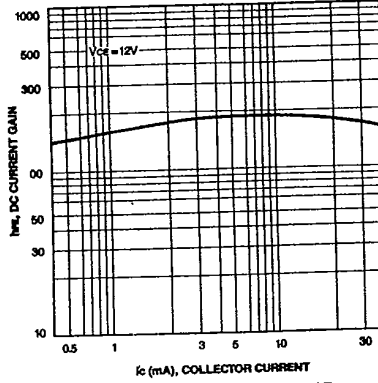
NPN EPITAXIAL SILICON TRANSISTOR

T-31-17

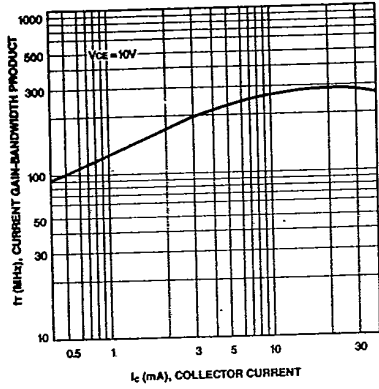
STATIC CHARACTERISTIC



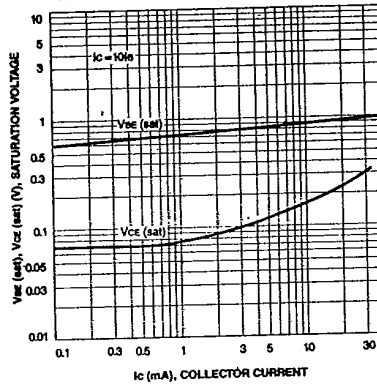
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

